Amendments to the Claims:

1. (currently amended): A method of forming a polysilicon resistor, the method comprising:

providing a substrate, the substrate comprising a dielectric layer;

forming a polysilicon layer on the dielectric layer;

doping the polysilicon layer with first type dopants and second type dopants;

defining a polysilicon resistor pattern on the polysilicon layer and removing ~~portions of~~ the polysilicon layer and the dielectric layer outside the polysilicon resistor pattern down to the surface of the substrate, the remainder of the polysilicon layer comprising at least a high resistance region and a low resistance region; and

forming a salicide layer on the remainder ~~portions~~ of the polysilicon layer within the low resistance region.

2. (original): The method of claim 1 wherein the first type dopants comprise N-type dopants and the second type dopants comprise P-type dopants.

3. (original): The method of claim 1 wherein a dosage of the first type dopants and a dosage of the second type dopants have the same order of magnitude.

4. (currently amended): The method of claim 1 further comprising forming a salicide block on the remainder ~~portions~~ of the polysilicon layer within the high resistance region.

5. (original): The method of claim 1 further comprising:

forming an inter layer dielectric on the substrate, the inter layer dielectric comprising at least a contact hole connecting to the salicide layer; and

forming a conductive layer on portions of the inter layer dielectric and within the contact hole.

6. (original): The method of claim 1 wherein the low resistance region is at the either side of

the high resistance region.

7. (original): A method of forming a high resistance region of a polysilicon resistor, the method comprising:

providing a substrate, the substrate comprising a dielectric layer;

forming a polysilicon layer on the dielectric layer; and

doping the polysilicon layer with first type dopants and second type dopants, thus forming the high resistance region on portions of the polysilicon layer.

8. (original): The method of claim 7 wherein the first type dopants comprise N-type dopants and the second type dopants comprise P-type dopants.

9. (original): The method of claim 7 wherein a dosage of the first type dopants and a dosage of the second type dopants have the same order of magnitude.

10. (original): The method of claim 7 further comprising forming a salicide block on the portions of the polysilicon layer within the high resistance region.

11. (original): The method of claim 7 further comprising forming a salicide layer on the portions of the polysilicon layer except the high resistance region, thus forming at least a low resistance region of the polysilicon resistor.

12. (original): The method of claim 11 further comprising:

forming an inter layer dielectric on the substrate, the inter layer dielectric comprising at least a contact hole connecting to the salicide layer; and

forming a conductive layer on portions of the inter layer dielectric and within the contact hole.

13. (original): The method of claim 11 wherein the low resistance region is at the either side

of the high resistance region.